

PIN DIODE

Low Magnetic Switching Diode For MR Application RoHS Compliant

GENERAL DESCRIPTION

With high isolation, low loss, and low distortion characteristics, this Microsemi packaged PIN diode is suited for antenna switch applications where size and power handling capability are critical. The assembly is designed for MRI applications where low susceptance is necessary. The surface mount package is ideal for high volume automated assembly applications.

Its advantages also include the low forward bias resistance and high zero bias impedance that are essential for low loss, high isolation, and wide bandwidth antenna switch performance. Its square design makes this device ideal for use with automatic insertion equipment.



KEY FEATURES

- High Power Surface Mount Package.
- Specified low distortion, low loss.
- Low bias current requirements.
- High zero bias impedance.
- Low magnetic signature for MR applications.
- Compatible with automatic insertion equipment.
- RoHS compliant ¹

¹ The UMX9501FMR is supplied with a RoHS compliant matte tin finish.

Consult factory for details.

APPLICATION/BENEFITS

- Low Loss T/R Switching.
- MRI Switching.
- Available on Tape & Reel



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ABSOLUTE MAXIMUM RATINGS @ 25°C (UNLESS OTHERWISE SPECIFIED)

| Rating | Symbol | Value | Unit |
|---|------------------|-------------|------|
| Maximum Reverse Voltage | V_R | 150 | V |
| Average Power Dissipation | P_D | 4 | W |
| Storage Temperature Range | T _{STG} | -65 to 175 | °C |
| Operating Temperature Range | T _{OP} | - 65 to 175 | °C |
| Thermal resistance. (25°C contacts, free air) | R_{θ} | 37.5 | °C/W |

ELECTRICAL PERFORMANCE @ 25°C (UNLESS OTHERWISE SPECIFIED)

| Parameter | Symbol | Conditions | Min | Тур | Max | Units |
|--|----------------|---|-----|------|------|-------|
| Total Capacitance | C _T | $V_R = 50V$ f = 1 MHz | | 0.75 | 0.9 | pF |
| Series Resistance | Rs | I _F = 50 mA f = 100 MHz | | 0.5 | 0.75 | Ohms |
| Parallel Resistance | R _P | f = 100MHz Vr = 0V | 5 | 10 | | kOhms |
| Carrier Lifetime | TL | I _F = 10 mA | 2 | 4 | | μs |
| Reverse Current | I _R | V _R = 50 | | | 10 | μΑ |
| Forward Voltage | V _F | I _F = 100mA | | | 1.0 | ٧ |
| Transmit Harmonic Distortion | | P_{IN} = 50 W f = 50 MHz I_F = 50 mA | 80 | | | -dB |
| Receive 3rd Order Harmonic Distortion | | $F = 100 \text{ MHz}$ $V = 0 \text{ V}$ $F_A = 50 \text{ MHz}$ $F_B = 51 \text{ MHz}$ | 60 | | | -dB |



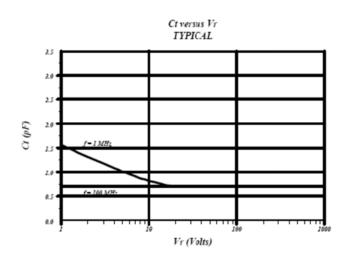
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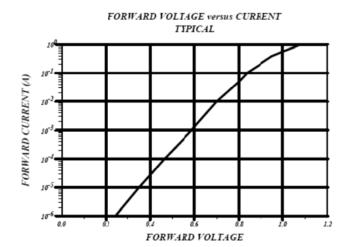
TYPICAL RS VS IF

Rs versus If TYPICAL 10² 10

TYPICAL CT VS VR



IF CURVE

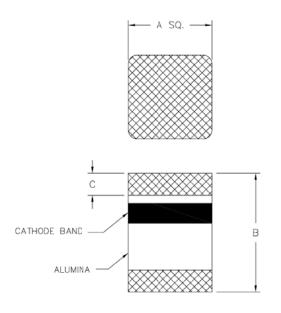




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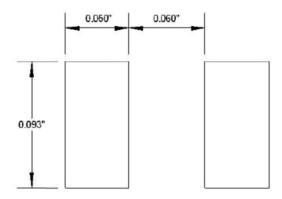
PACKAGE OUTLINE





| DIM | INCHES | | | MM | | |
|-----|--------|-----|-------|-------|-----|-------|
| DIN | MIN | TYP | MAX | MIN | TYP | MAX |
| А | 0.080 | _ | 0.095 | 2.032 | _ | 2.413 |
| В | 0.115 | _ | 0.135 | 2.921 | - | 3.429 |
| С | 0.008 | _ | 0.030 | 0.203 | _ | 0.762 |

FOOTPRINT



NOTES:

- 1. These dimensions will match the terminals and provide for additional solder fillets at the outboard ends at least as wide as the terminals themselves, assuming accuracy of placement within 0.005".
- If the mounting method chosen requires use of an adhesive separate from the solder compound, a round (or square) spot of cement should be centrally located.

Revision History

| Revision Level / Date | Para. Affected | Description |
|-----------------------|----------------|-----------------|
| 1 / 14 September 15 | - | Initial Release |